

General Description

The MAX6819/MAX6820 are power-supply sequencers for dual-voltage microprocessors (µPs) and multivoltage systems. These devices monitor a primary supply voltage and enable/disable an external N-channel MOSFET switch for a secondary supply voltage. The MAX6819/MAX6820 control local component voltage sequencing when system power-on/power-off characteristics cannot be guaranteed (supplies come from a multivoltage system bus, silver box, or must be sequenced in different modes for components on the same board). These small power-supply sequencers improve system reliability.

The MAX6819/MAX6820 include an internal voltage reference/comparator with externally adjustable thresholds to monitor the primary power supply. When the primary supply is below the desired threshold, an external secondary supply MOSFET switch is disabled. When the primary supply exceeds the threshold, an internal charge pump is activated and the external MOSFET switch is enabled to connect the secondary supply to the load. The charge pump fully enhances the N-channel MOSFET switch to provide a very low RDS-ON voltage drop. The devices can be connected to support various supply sequencing priorities such as VI/O before VCORE or VCORE before VI/O.

The MAX6819 features a logic-driven EN input to enable/disable the external MOSFET drive and includes an internally fixed 200ms enable timeout period (VPRIMARY GOOD to VSECONDARY ENABLE). The MAX6820 allows the enable timeout period to be adjusted with a single external capacitor. Both devices are specified over the automotive temperature range (-40°C to +125°C) and are available in space-saving 6-pin SOT23 packages.

Applications

Dual-Voltage Microprocessors Multivoltage Systems Digital Signal Processors Power PC™ Series Processors

Pin Configurations and Typical Operating Circuits continued at end of data sheet.

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Features

- ♦ Adjustable Primary Supply Voltage Monitor (Monitors Down to 0.62V)
- ♦ Internal Charge Pump to Enhance External Secondary Supply N-Channel MOSFET Switch
- ♦ Delay from Primary Supply Good to Secondary Supply Enabled

Factory Fixed 200ms (MAX6819) Capacitor Adjustable (MAX6820)

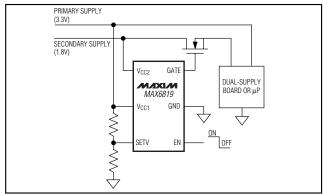
- **♦ Logic Driven ENABLE Input (MAX6819)**
- ♦ Immune to Short Voltage Transients
- **♦ Few External Components**
- ♦ -40°C to +125°C Operating Temperature Range
- ♦ Small 6-Pin SOT23 Package

Ordering Information

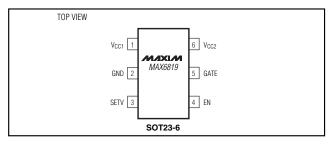
PART	TEMP. RANGE	TEMP. RANGE PIN- PACKAGE	
MAX6819 ∪T-T	-40°C to +125°C	6 SOT23-6	AARF
MAX6820 ∪T-T	-40°C to +125°C	6 SOT23-6	AARG

Products must be ordered in 2,500 piece increments.

Typical Operating Circuits



Pin Configurations



MIXIM

Maxim Integrated Products 1

ABSOLUTE MAXIMUM RATINGS

Referenced to GND	Continuous Power Dissipation (T _A = +70°C)
V _{CC1} , V _{CC2} , EN0.3V to +6.0V	6-Pin SOT23 (derate 8.7mW/°C above +70°C)696mW
SETV, SETD0.3V to the higher of (V _{CC1} + 0.3V) and	Operating Temperature Range40°C to +125°C
$(V_{CC2} + 0.3V)$	Junction Temperature+150°C
GATE0.3V to +12.0V	Storage Temperature Range65°C to +150°C
Input Current/Output Current (all pins)20mA	Lead Temperature (soldering 10s)+300°C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

 $(V_{CC1} \text{ or } V_{CC2} > +2.125 \text{V to } +5.5 \text{V}, T_A = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}, \text{ unless otherwise specified. Typical values are at } T_A = +25 ^{\circ}\text{C}.)$ (Note 1)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	
Operating Voltage Range	V _{CC1} , V _{CC2}	(Note 2)	0.9		5.5	V	
V _{CC1} , V _{CC2} Supply Current	Icc	V _{CC1} = V _{CC2} = +3.3V		60	120	μΑ	
V _{CC1} , V _{CC2} Disable Mode Current		$V_{CC1} = V_{CC2} = +3.3V$, $EN = GND$		20		μΑ	
V V Clay Data (Nata 2)		MAX6819				\//-	
V _{CC1} , V _{CC2} Slew Rate (Note 3)		MAX6820 (Note 4)	1.2/t _{DELAY}			V/s	
Undervoltage Lockout (UVLO)	V _{UVLO}		1.875	2.0	2.125	V	
SETV Threshold	V _{TH}	V _{SETV} rising, enables GATE	0.602	0.618	0.634	V	
SETV Input Current		(Note 3)		10	100	nA	
SETV Threshold Hysteresis		V _{SETV} falling, disables GATE		-1		%	
SETV to GATE Delay	tDELAY	V _{SETV} > V _{TH} , V _{EN} ≥ 2V (MAX6819)	140	200	280	ms	
SETD Ramp Current (MAX6820)	ISETD	V _{CC1} or V _{CC2} > +2.125V	400	500	600	nA	
SETD Voltage (MAX6820)	V _{SETD}	V _{CC1} or V _{CC2} > +2.125V	1.210	1.242	1.273	V	
SETD Threshold Hysteresis (MAX6820)		V _{SETD} falling		-62		mV	
GATE Turn-On Time	ton	C _{GATE} = 1500pF, V _{CC2} = +3.3V, V _{GATE} = +7.8V	0.5	1.5	10	ms	
GATE Turn-Off Time	toff	C _{GATE} = 1500pF, V _{CC2} = +3.3V, V _{GATE} = +0.5V		30		μs	
GATE Voltage	VGATE	With respect to V_{CC2} (Note 2) RGATE > $50M\Omega$ to V_{CC2}	4.5	5.5	6.0	- V	
		With respect to V_{CC2} (Note 2) RGATE > $5M\Omega$ to V_{CC2}	4.0		6.0		
EN Input Voltage	VIL	V _{CC1} or V _{CC2} > +2.125V to + 5.5V		-	0.4	V	
Livinput voltage	VIH	VOOT 01 VOOZ > TZ.125V 10 T 0.5V	2.0				

Note 1: 100% production tested at $T_A = +25$ °C. Specifications over temperature limit are guaranteed by design.

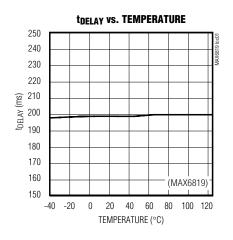
Note 2: Either V_{CC1} or V_{CC2} must be > 2.125V. The other supply can go to 0.

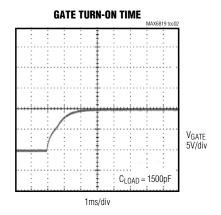
Note 3: Guaranteed by design, not production tested.

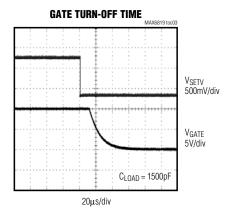
Note 4: $t_{DELAY}(s) = 2.484e^6 \times C_{SET}$

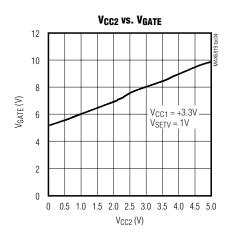
Typical Operating Characteristics

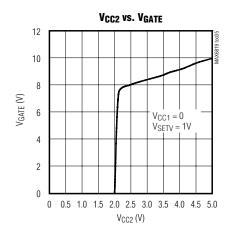
 $(T_A = +25^{\circ}C, \text{ unless otherwise noted.})$

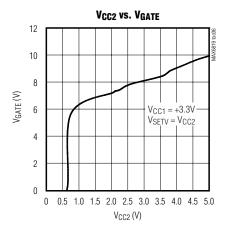






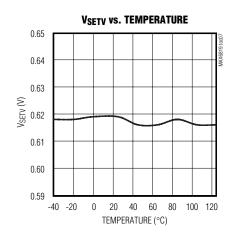


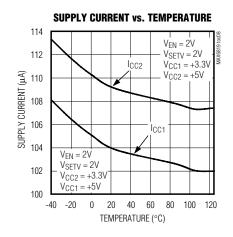


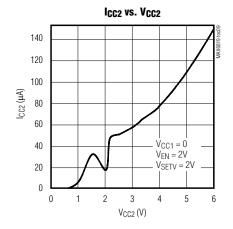


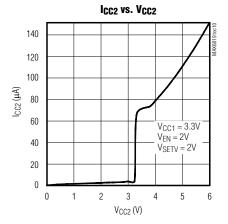
Typical Operating Characteristics (continued)

 $(T_A = +25^{\circ}C, \text{ unless otherwise noted.})$









Pin Description

PIN			FUNCTION	
MAX6819	MAX6820	NAME	FUNCTION	
1	1	VCC1	Supply Voltage 1. Either V _{CC1} or V _{CC2} must be greater than the UVLO to enable external MOSFET drive.	
2	2	GND	Ground	
3	3	SETV	Sequence Threshold Set. Connect to an external resistor-divider network to set the V _{CC1} threshold that enables GATE turn-on. The internal reference is 0.618V.	
4	_	EN	Active-High Enable. GATE drive is enabled t _{DELAY} after EN is driven high. GATE drive is immediately disabled when EN is driven low. Connect to the higher of V _{CC1} and V _{CC2} if not used.	
_	4	SETD	GATE Delay Set Input. Connect an external capacitor from SETD to GND to adjust the delay from SETV > V _{TH} to GATE turn-on. t _{DELAY} (s) = 2.484e6 x C _{SET} (F).	
5	5	GATE	GATE Drive Output. GATE drives an external N-channel MOSFET to connect V_{CC2} the load. GATE drive enables t_{DELAY} after SETV exceeds V_{TH} and ENABLE is drive high. GATE drive is immediately disabled when SETV drops below V_{TH} or ENABLE driven low. When enabled, an internal charge pump drives GATE to V_{CC2} + 5.5V to fully enhance the external N-channel MOSFET.	
6	6	V _{CC2}	Supply Voltage 2. Either V _{CC1} or V _{CC2} must be greater than the UVLO to enable external MOSFET drive.	

Detailed Description

Many dual-supply processors or multivoltage boards require one power supply to rise to the proper operating voltage before another supply is applied. Improper sequencing can lead to chip latchup, incorrect device initiation, or long-term reliability degradation. If the various supply voltages are not locally generated (coming from a main system bus, an externally purchased silver box, or a nonsequenced power management chip), power-on and power-off sequencing can be difficult to control or predict. Supply loading can affect turn-on/turn-off times from board to board.

The MAX6819/MAX6820 provide proper local voltage sequencing in multisupply systems. The sequencers use an external N-channel MOSFET to switch the secondary supply to the load only when the primary supply is above a desired operating voltage threshold. The N-channel MOSFET operates in a default off mode when the primary supply is below the desired threshold or if neither supply exceeds the sequencer's UVLO level.

When the primary supply voltage is above the set threshold, the external MOSFET is driven on. An internal charge pump fully enhances the external MOSFET by providing a gate-to-source voltage (VGS) of +5.5V (typ). The charge pump fully enhances the MOSFET to yield a low drain-to-source impedance (RDS(ON)) for

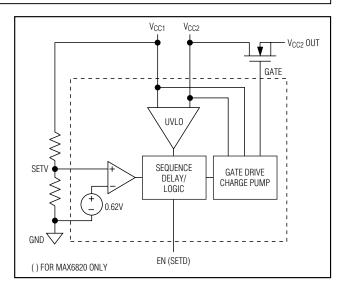


Figure 1. Functional Diagram

reduced switch voltage drop. The MOSFET is never driven on unless the sequencer can provide a minimum VGS enhancement, ensuring that the switch MOSFET never operates in its higher impedance linear range.

Either supply may act as the primary source, regardless of the voltage level, provided that V_{CC1} or V_{CC2} is greater than 2.125V (Figure 1 and Figure 2).

Applications Information

Adjusting tDELAY

The MAX6820 features a capacitor adjustable sequence delay. The adjustable delay provides power sequencing for a wide range of devices with different power-supply delay requirements. Connect a capacitor (CSET) between SETD and GND to adjust the delay time (Figure 2). Calculate the sequence delay time as follows:

 $t_{DELAY}(s) = 2.484e6 \times C_{SET}$

Setting Threshold Voltage VTH

The threshold voltage is the minimum $V_{\rm CC1}$ voltage at which $V_{\rm CC2}$ turn-on is acceptable. To monitor voltages higher than the threshold voltage, connect external resistors as a voltage-divider to SETV, and calculate $V_{\rm TH}$ as follows:

$$R1 = R2 (V_{TH} / V_{TRIP} - 1)$$

Where V_{TH} is the desired threshold voltage and $V_{TRIP} = 0.618V$ (Figure 2).

Since SETV input current is 10nA (typ), high value resistors can be used.

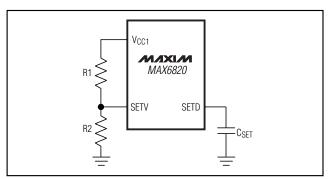


Figure 2. tDFLAY (MAX6820 ONLY) and VTH Adjust

Selecting the Pass MOSFET

The external pass MOSFET is connected in series with the sequenced power-supply source. Since the load current and the MOSFET drain-to-source impedance (RDS) determine the voltage drop, the on characteristics of the MOSFET affect the load supply accuracy. The MAX6819/MAX6820 fully enhance the external MOSFET out of its linear range to ensure the lowest drain-to-source on impedance. For highest supply accuracy/lowest voltage drop, select a MOSFET with an appropriate drain-to-source on impedance for a gate-to-source bias of 4.5V to 6.0V.

Gate Drive Characteristics

The MAX6819/MAX6820 internal charge pump drives the N-channel MOSFET with a gate-to-source voltage (VGS) of 5.5V, ensuring low MOSFET on-resistance RDS(ON). The charge pump drives the high-impedance capacitive load of a MOSFET gate input.

Loading the GATE output resistively adds load current and reduces gate drive capability. The internal charge pump does not require external capacitors.

The external pass MOSFET is disabled, and charge pump circuitry is turned off when neither $V_{\rm CC1}$ nor $V_{\rm CC2}$ are above the 1.875V UVLO or EN is low.

Logic Driven Supply Sequencing

The MAX6819 offers a logic-compatible enable input (EN) that allows digital devices to control sequencing. When the TTL/CMOS-compatible EN input is logic low, the GATE output is low. When the EN input is logic high (and SETV is above the monitor threshold), the GATE output is enabled after an internally fixed 200ms delay. For a logic controlled sequencer when voltage monitoring is not desired, connect SETV to VCC1 or VCC2 > 0.62V (Figure 3).

Sequencing Three or More Supplies

Cascade multiple MAX6819/MAX6820 to sequence more than two supplies. Daisy-chaining devices allows one sequencer to monitor the passed voltage of an upstream sequencer through the SETV comparator inputs. EN allows any sequencer to be shut down independent of the SETV levels. Figure 4 shows an example of a three-supply system in which the first supply must come up before the second supply and the third supply must yield for both supplies.

Negative-Going Voltage Transient Immunity

The MAX6819/MAX6820 power-supply voltage sequencers are relatively immune to short-duration (pulse width), negative-going voltage transients (Figure 5). However, the amplitude of the transient is inversely proportional to its pulse width.

_Chip Information

TRANSISTOR COUNT: 638 PROCESS: BICMOS

____ /N/1XI/W

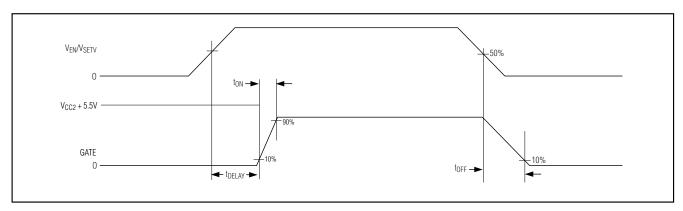


Figure 3. Timing Diagram

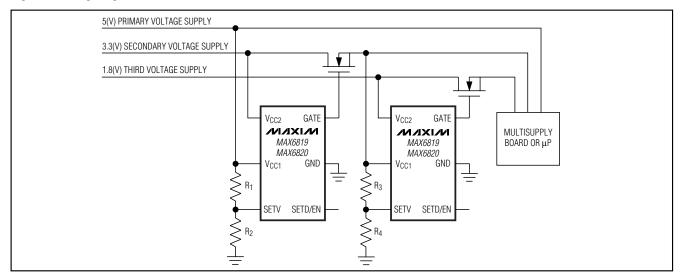


Figure 4. Sequencing Three Power Supplies

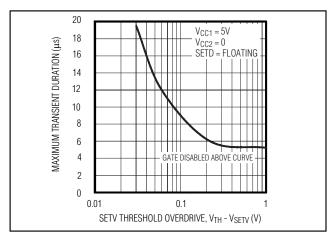
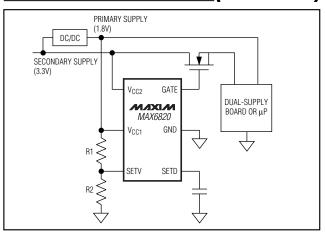


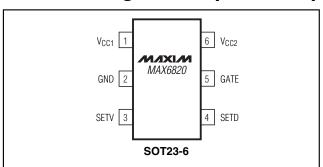
Figure 5. Maximum Transient Duration vs. SETV Threshold in Overdrive



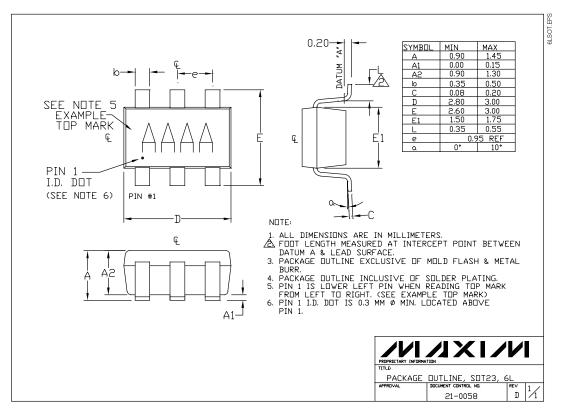
Typical Operating Circuits (continued)



_Pin Configurations (continued)



Package Information



Maxim cannot assume responsibility for use of any circuitry other than circuitry entirely embodied in a Maxim product. No circuit patent licenses are implied. Maxim reserves the right to change the circuitry and specifications without notice at any time.

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